

P-Channel 60 V (D-S) 150 °C MOSFET

DESCRIPTION

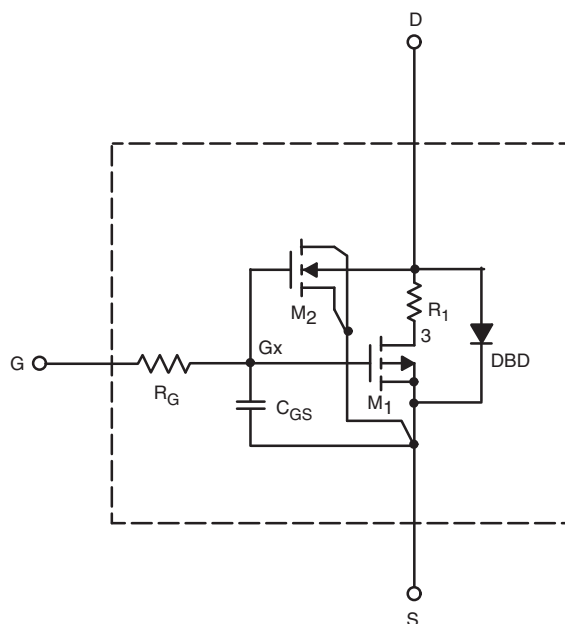
The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge

SUBCIRCUIT MODEL SCHEMATIC



Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



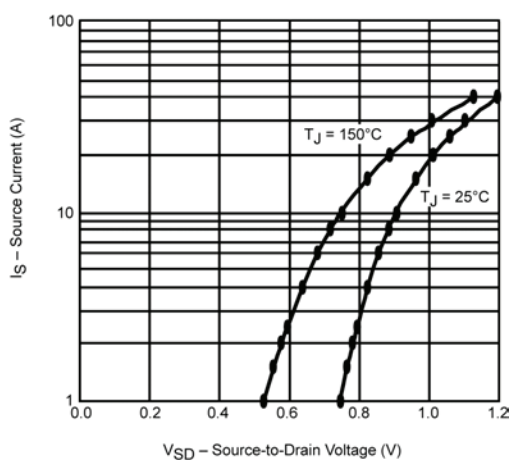
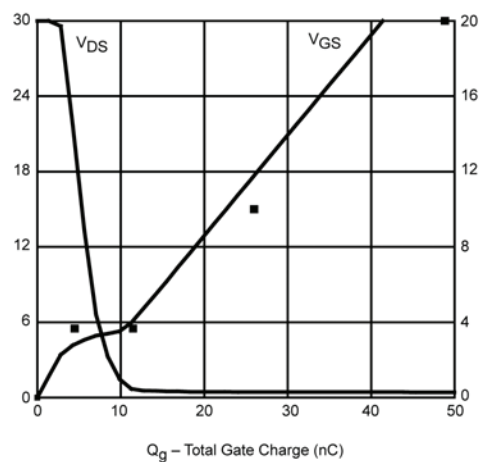
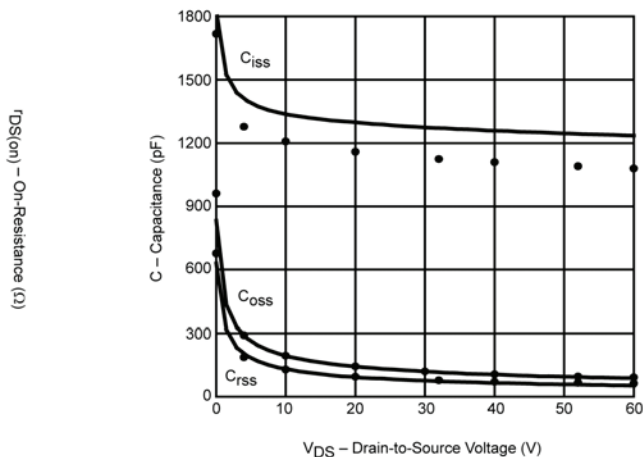
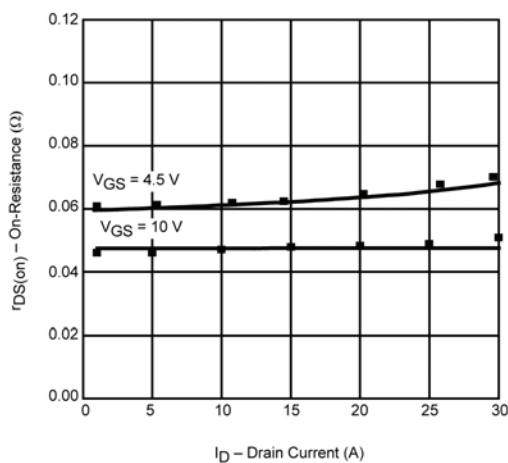
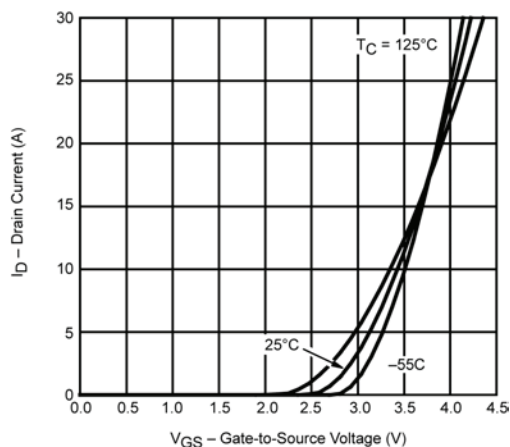
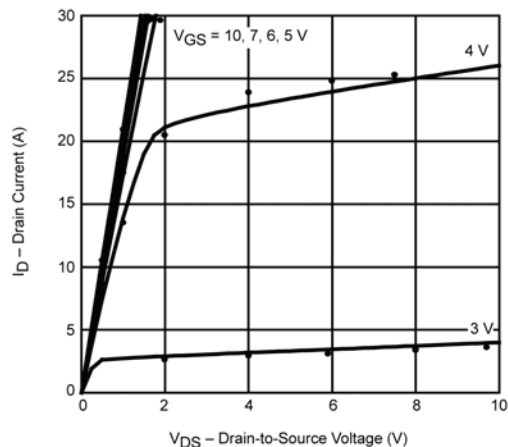
SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	2	-	V
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}$, $V_{GS} = -10\text{ V}$	104	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$, $I_D = -10\text{ A}$	0.047	0.048	Ω
		$V_{GS} = -10\text{ V}$, $I_D = -10\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	0.083	-	
		$V_{GS} = -10\text{ V}$, $I_D = -10\text{ A}$, $T_J = 150\text{ }^{\circ}\text{C}$	0.093	-	
		$V_{GS} = -4.5\text{ V}$, $I_D = -5\text{ A}$	0.060	0.061	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}$, $I_D = -10\text{ A}$	20	22	S
Diode Forward Voltage	V_{SD}	$I_S = -10\text{ A}$, $V_{GS} = 0\text{ V}$	-1	-1	V
Dynamic^b					
Input Capacitance	C_{iss}	$V_{DS} = -25\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	1285	1140	pF
Output Capacitance	C_{oss}		130	130	
Reverse Transfer Capacitance	C_{rss}		85	90	
Total Gate Charge	Q_g	$V_{DS} = -30\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -10\text{ A}$	23	26	nC
Gate-Source Charge	Q_{gs}		4.5	4.5	
Gate-Drain Charge	Q_{gd}		7	7	

Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.



COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25^\circ\text{C}$, unless otherwise noted)



Note

- Dots and squares represent measured data.